

# 74AUP1G04

### Low power single inverter gate

### Features

- High speed: t<sub>PD</sub> = 4.3 ns (max.) at V<sub>CC</sub> = 2.3 V
- Power down protection on inputs and outputs
- Balanced propagation delays: t<sub>PLH</sub> ≈ t<sub>PHL</sub>
- Operating voltage range:
   V<sub>CC</sub> (opr) = 1.2 to 3.6 V
- Low power dissipation: I<sub>CC</sub> = 1 µA (max.) at T<sub>A</sub> = 85 °C
- Latch-up performance exceeds 300 mA (JESD 78, Class II)
- ESD performance:
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

### **Applications**

- Mobile phones
- Personal digital assistants (PDAs)



### Description

The 74AUP1G04 is a low voltage CMOS single inverter gate fabricated with sub-micron silicon gate and double-layer metal wiring  $C^2MOS$  technology. It is ideal for 1.2 to 3.6 V operations and low power and low noise applications.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2kV ESD immunity and transient excess voltage.

#### Table 1. Device summary

Order code	Package	Packing
74AUPG04DTR	DFN6L (1.2 x 1 mm)	Tape and reel
74AUPG04GTR	SOT-665 (1.6 x 1.6 mm)	Tape and reel

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## 1 Pin settings

### 1.1 Pin connection





## 1.2 Pin description

DFN pin number	SOT pin number	Symbol	Name and function
1	1	NC	Not connected
2	2	А	Data input
3	3	GND	Ground (0V)
4	4	В	Data output
5	-	NC	Not connected
6	5	V <sub>CC</sub>	Positive supply voltage



### 1.3 Truth table





#### Table 3. Truth table

Α	В
L	н
Н	L

#### Figure 3. Input and output equivalent circuit



## 2 Maximum rating

Stressing the device above the rating listed in the "absolute maximum ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage	-0.5 to +4.6	V
VI	DC input voltage	-0.5 to +4.6	V
Vo	DC output voltage ( $V_{CC} = 0 V$ )	-0.5 to +4.6	V
Vo	DC output voltage (high or low state)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC input diode current	-20	mA
Ι <sub>ΟΚ</sub>	DC output diode current	-50	mA
۱ <sub>0</sub>	DC output current	±50	mA
I <sub>CC</sub>	DC supply current per supply pin	±100	mA
I <sub>GND</sub>	DC ground current per supply pin	±100	mA
PD	Power dissipation	200	mW
T <sub>stg</sub>	Storage temperature	-65 to +150	°C
TL	Lead temperature (10 sec)	260	°C

Table 4. Absolute maximum ratings

### 2.1 Recommended operating conditions

#### Table 5. Recommended operating conditions

Symbol	Р	Value	Unit	
V <sub>CC</sub>	Supply voltage	1.2 to 3.6	V	
VI	Input voltage	0 to V <sub>CC</sub>	V	
Vo	Output voltage	0 to V <sub>CC</sub>	V	
T <sub>op</sub>	Operating temperature	-40 to 85	°C	
		V <sub>CC</sub> = 3.0 to 3.6 V	10	ns/V
dt/dv	Input rise and fall time	$V_{CC}$ = 2.3 to 2.7 V	20	ns/V
		V <sub>CC</sub> = 1.2 to 1.95 V	100	ns/V



## **3** Electrical characteristics

				Va	Value		Value		
Symbol	Parameter	V <sub>CC</sub> (V)	Test condition	25	°C	-40 to 85 °C		Unit	
				Min	Max	Min	Max		
		1.2 to 1.95		$0.65 V_{CC}$		0.65 V <sub>CC</sub>			
V <sub>IH</sub>	High level input voltage	2.0 to 2.7		1.6		1.6		V	
		2.75 to 3.6		2.0		2.0			
		1.2 to 1.95			0.35 V <sub>CC</sub>		$0.35V_{CC}$		
VIL	Low level input	2.0 to 2.7			0.7		0.7	V	
	ge	2.75 to 3.6			0.8		0.8		
		1.2 to 3.6	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> – 0.2		V <sub>CC</sub> – 0.2			
	High level output voltage	3.0	I <sub>OH</sub> = -10 mA	2.45		2.4		V	
V <sub>OH</sub>		2.3	I <sub>OH</sub> = -6 mA	1.85		1.8			
		1.65	I <sub>OH</sub> = -4 mA	1.30		1.25			
		1.4	I <sub>OH</sub> = -2 mA	1.10		1.05			
		1.2	I <sub>OH</sub> = -1 mA	1.00		0.95			
		1.2 to 3.6	l <sub>O</sub> = 100 μA		0.15		0.20		
		3.0	l <sub>O</sub> = 10 mA		0.50		0.55		
N	Low level	2.3	I <sub>O</sub> = 6 mA		0.35		0.40	V	
VOL	output voltage	1.65	I <sub>O</sub> = 4 mA		0.35		0.40	v	
		1.4	I <sub>O</sub> = 2 mA		0.25		0.30		
		1.2	I <sub>O</sub> = 1 mA		0.20		0.25		
I <sub>I</sub>	Input leakage current	0 to 3.6	$V_{I} = GND \text{ to } 3.6$		±0.1		±0.5	μA	
I <sub>off</sub>	Power off leakage current	0	$V_1 \text{ or } V_0 = 0 \text{ to}$ 3.6 V		±0.1		±1.0	μA	
I <sub>CC</sub>	Quiescent supply current	1.2 to 3.6	$V_{I} = V_{CC}$ or GND		0.1		1	μA	
$\Delta I_{CC}$	I <sub>CC</sub> increment per input	3.3	$V_{I} = V_{CC} - 0.6V,$ $I_{O} = 0$		80		100	μA	

#### Table 6.DC specifications



		Vee		Value			
Symbol	Parameter	V <sub>CC</sub> (V)	Q (= [)	25 °C -40 to 85 °C		Unit	
			С <sub>L</sub> (рг)	Тур	Min	Max	
		1.1 to 1.3		8.0		12.4	
		1.4 to 1.6		4.2		6.6	
		1.65 to 1.95	5	3.2		5.1	
		2.3 to 2.7		2.3		3.1	
		3.0 to 3.6		1.9		2.5	ns
	Propagation delay time	1.1 to 1.3	10	8.6		13	
		1.4 to 1.6		4.6		7	
		1.65 to 1.95		3.5		5.3	
		2.3 to 2.7		2.4		3.5	
		3.0 to 3.6		2.0		2.9	
<sup>I</sup> PLH, <sup>I</sup> PHL		1.1 to 1.3	15	9.1		13.3	
		1.4 to 1.6		5.6		7.5	
		1.65 to 1.95		3.8		5.7	
		2.3 to 2.7		2.6		3.7	
		3.0 to 3.6		2.2		3.1	
		1.1 to 1.3		10.5		16	
		1.4 to 1.6		5.5		9	
		1.65 to 1.95	30	4.3		6.7	
		2.3 to 2.7		3.1		4.3	1
		3.0 to 3.6		2.7		3.8	

#### Table 7. AC electrical characteristics

#### Table 8. Capacitive characteristics

Symbol	Parameter	V <sub>CC</sub> (V)	V <sub>CC</sub> Test (V) condition		Unit		
				Min	Тур	Max	
C.		0	$V_I = 0 \text{ or } V_{CC}$		3		рF
	input capacitance	3.6	$V_{I} = 0 \text{ or } V_{CC}$		6		рі
Co	Output capacitance	3.6	$V_{I} = 0 \text{ or } V_{CC}$		6		pF
C <sub>PD</sub>	Power dissipation capacitance	3.6	f = 10 MHz		32		pF



## 4 Test circuit





#### Table 9. Test setting

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Test	Switch
t <sub>PLH</sub> , t <sub>PHL</sub>	Open

#### Table 10. Symbol and values for test circuit and waveform

Symbol	v <sub>cc</sub>						
Symbol	1.2 ± 0.1 V	1.5 ± 0.1 V	1.8 ± 0.15 V	2.5 ± 0.2 V	3.3 ± 0.3 V		
CL	5, 10, 15, 30 pF	5, 10, 15, 30 pF					
RL	500 Ω	500 Ω	500 Ω	500 Ω	500 Ω		
V <sub>M</sub>	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	1.5		
$V_{IH}$	V <sub>CC</sub>	V <sub>CC</sub>	V <sub>CC</sub>	V <sub>CC</sub>	V <sub>CC</sub>		
$t_r = t_f$	≤ 2 ns	≤2 ns	≤2 ns	≤2 ns	≤2 ns		

 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )





Figure 5. Waveform: propagation delay (f = 1 MHz; 50% duty cycle)



## 5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK<sup>®</sup> packages. These packages have a Lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.





Symbol	Millimeters					
	Тур	Min	Мах			
A	0.50	0.45	0.55			
A1	0.02	0	0.05			
A3	0.127					
b	0.20	0.15	0.25			
D	1.20	1.15	1.25			
E	1	0.95	1.05			
е	0.40					
L	0.35	0.30	0.40			
L1	0.45	0.40	0.50			

 Table 11.
 DFN6L (1.2 x 1 mm) package mechanical data

Figure 7. DFN6L (1.2 x 1 mm) package footprint







Figure 8. SOT-665 (1.6 x 1.6 mm) package outline

Table 12.	SOT665 (	(1.6 x 1.6 mm) mechanical data
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Symbol	Millimeters			
	Тур	Min	Мах	
A		0.50	0.60	
bp		0.17	0.27	
С		0.08	0.18	
D		1.5	1.7	
E		1.1	1.3	
e	1			
e1	0.5			
He		1.5	1.7	
Lp		0.1	0.3	





Figure 9. SOT-665 (1.6 x 1.6 mm) package footprint





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Figure 11. DFN6L (1.2 x 1 mm) reel information drawing (back view)

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Figure 12. DFN6L (1.2 x 1 mm) reel information drawing (front view)

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Figure 13. SOT-665 (1.6 x 1.6 mm) carrier tape information

Figure 14. SOT-665 (1.6 x 1.6 mm) reel information



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Value <sup>(1)</sup>	R1	R2	R3	eint (at hub)	e1	W1	W2	W3
Min	12.8	175	59.5	8.4	1.5	8.4		7.9
Тур	13	180	60	8.4		8.4		9.4
Max	13.2	185	60.5	10		10	14.4	10.9

Table 13. SOT-665 (1.6 x 1.6 mm) reel description

1. Millimeters.



## 6 Revision history

#### Table 14.Document revision history

Date	Revision	Changes
28-Mar-2008	1	Initial release.



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